

SMD Schottky Barrier Diode

COMCHIP
SMD Diodes Specialist

CDBU001A

I_o = 100mA

V_R = 30 Volts



Features

Designed for mounting on small surface

Extremely thin package

Low stored charge

Majority carrier conduction

Mechanical data

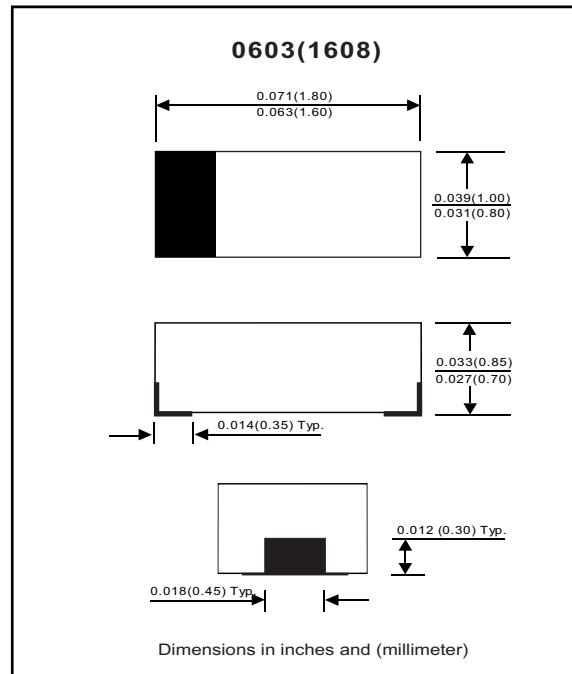
Case: 0603 (1608) Standard package, molded plastic

Terminals: Solder plated, solderable per MIL-STD-750, method 2026

Polarity: Indicated by cathode band

Mounting position: Any

Weight: 0.003 gram (approximately)



Maximum Rating (at TA = 25 °C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Repetitive peak reverse voltage		V _{RRM} , V _R			30	V
Average forward current		I _o			100	mA
Forward current , surge peak	8.3 ms single half sine-wave superimposed on rate load (JEDEC method)	I _{FSM}		500		mA
Power Dissipation		P _D			150	mW
Storage temperature		T _{STG}	-40		+125	°C
Junction temperature		T _j	-40		+125	°C

Electrical Characteristics (at TA= 25 °C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Forward voltage 1	IF = 0.1 mA DC	V _F			0.24	V
Forward voltage 2	IF = 1 mA DC	V _F			0.32	V
Forward voltage 3	IF = 10 mA DC	V _F			0.40	V
Forward voltage 4	IF = 30 mA DC	V _F			0.50	V
Forward voltage 5	IF = 100 mA DC	V _F			1.00	V
Reverse current	V _R = 25 V	I _R			2	uA
Capacitance between terminals	F=1MHz and 10V DC reverse voltage	C _T			6	pF

RATING AND CHARACTERISTIC CURVES (CDBU001A)

Fig. 1 - Forward characteristics

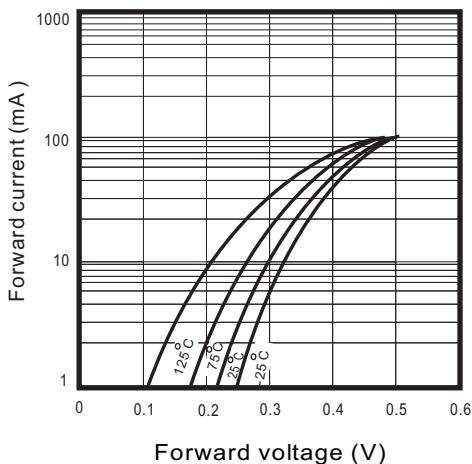


Fig. 2 - Reverse characteristics

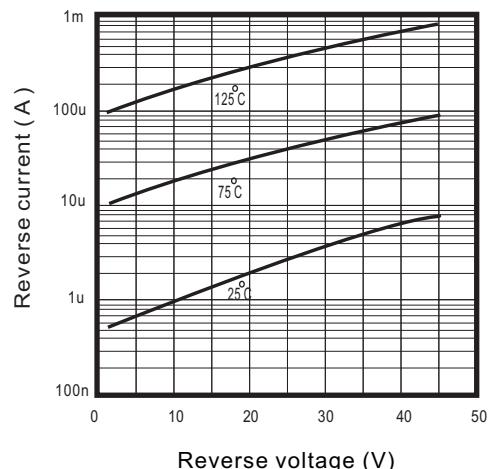


Fig. 3 - Capacitance between terminals characteristics

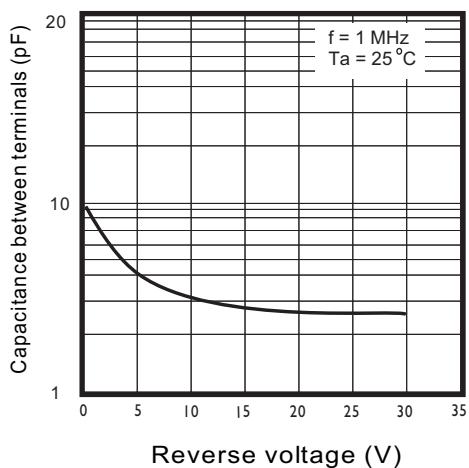


Fig. 4 - Current derating curve

